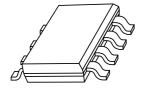
DISCRETE SEMICONDUCTORS

DATA SHEET



KMZ43TMagnetic field sensor

Product specification Supersedes data of 2003 Mar 26 2003 Sep 15





Magnetic field sensor

KMZ43T

DESCRIPTION

The KMZ43T is a sensitive magnetic field sensor, employing the magnetoresistive effect of thin-film permalloy. The sensor contains two galvanic separated Wheatstone bridges, at a relative angle of 45° to one another.

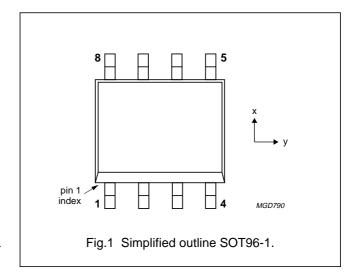
A rotating magnetic field in the x-y plane will produce two independent sinusoidal output signals, one a function of $+\cos(2\alpha)$ and the second a function of $+\sin(2\alpha)$, α being the angle between sensor and field direction (see Fig.3). Unlike the KMZ41⁽¹⁾, which needs a saturation field strength of 100 kA/m, the KMZ43T is suited to high precision angle measurement applications under low field conditions (saturation field strength 25 kA/m).

The sensor can be operated at any frequency between DC and 1 MHz.

The information in application notes AN00023 (Contactless Angle Measurement Using KMZ41 and UZZ9000) and AN00004 (Contactless Angle Measurement Using KMZ41 and UZZ9001) is applicable to the KMZ43T, but one should be aware of the difference in the bridge 1 output.

PINNING

PIN	SYMBOL	DESCRIPTION		
1	-V _{O1}	output voltage bridge 1		
2	-V _{O2}	output voltage bridge 2		
3	V _{CC2}	supply voltage bridge 2		
4	V _{CC1}	supply voltage bridge 1		
5	+V _{O1}	output voltage bridge 1		
6 +V _{O2}		output voltage bridge 2		
7 GND2		ground 2		
8 GND1		ground 1		



⁽¹⁾ The KMZ41 delivers a $+\sin(2\alpha)$ and a $-\cos(2\alpha)$ signal.

QUICK REFERENCE DATA

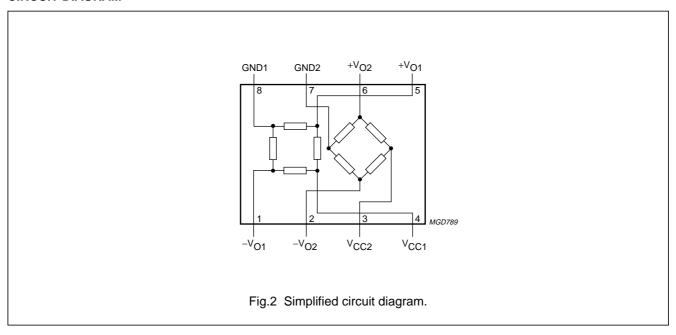
SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
Per bridge		•			
V _{CC}	supply voltage	_	5	9	V
S	sensitivity ($\alpha_2 = 0^\circ$; $\alpha_1 = 135^\circ$)	2.1	2.35	2.6	mV/°
V _{offset}	offset voltage per supply voltage	-2	_	+2	mV/V
R _{bridge}	bridge resistance per bridge	2.7	3.2	3.7	kΩ

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CIRCUIT DIAGRAM



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC1}	supply voltage bridge 1		_	9	V
V _{CC2}	supply voltage bridge 2		_	9	V
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	operating ambient temperature		-40	+150	°C

STIMULATING FIELD STRENGTH

CONDITIONS	MIN.	CONDITIONS	MIN.	MAX.	UNIT
H _{ext}	magnetic field strength	note 1	25	_	kA/m

Note

1. The minimum stimulating magnetic field in the x-y plane to ensure minimum angular inaccuracy specified in note 11 to Characteristics table.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	155	K/W

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CHARACTERISTICS

 T_{amb} = 25 °C and H_{ext} = 25 kA/m; V_{CC1} = 5 V; V_{CC2} = 5 V; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
ω	operating angular velocity		0	_	1	MHz
k	amplitude synchronism	note 9	99.5	100	100.5	%
TC _k	temperature coefficient of amplitude synchronism	T_{amb} = -40 to +150 °C; note 10	-0.01	0	-0.01	%/K
Δα	angular inaccuracy	note 11	0	0.05	0.1	deg
Per bridge				•		
V _{CC}	supply voltage		_	5	9	V
V _{offset} offset voltage per supply voltage		see Fig.3	-2	0	+2	mV/V
S	sensitivity	open circuit; note 1				
		$\alpha_1 = 135^{\circ} \text{ (bridge 1)}$	2.1	2.35	2.6	mV/°
		$\alpha_2 = 0^\circ$ (bridge 2)	2.1	2.35	2.6	mV/°
TC _S	temperature coefficient of sensitivity	T_{amb} = -40 to +150 °C; note 2	-0.25	-0.29	-0.33	%/K
V _{peak}	peak output voltage	note 3; see Fig.3	60	67	75	mV
TC _{Vpeak}	temperature coefficient of peak output voltage	$T_{amb} = -40 \text{ to } +150 ^{\circ}\text{C};$ note 4	-0.25	-0.29	-0.33	%/K
R _{bridge}	bridge resistance	note 5	2.7	3.2	3.7	kΩ
TC _{Rbridge} temperature coefficient of bridge resistance		$T_{amb} = -40 \text{ to } +150 ^{\circ}\text{C};$ note 6	0.28	0.32	0.35	%/K
TC _{Voffset}	temperature coefficient of offset voltage	$T_{amb} = -40 \text{ to } +150 ^{\circ}\text{C};$ note 7; see Fig.3	-4	0	+4	(μV/V)/K
FH	hysteresis of output voltage	note 8	0	0.05	0.18	%FS

Notes

1. Sensitivity changes with angle due to sinusoidal output.

$$2. \quad TC_S = 100 \times \frac{S_{T_2} - S_{T_1}}{S_{T_2} \times 190^{\circ}C} \ \, \text{where } T_1 = -40 \, \, ^{\circ}C; \, T_2 = 150 \, \, ^{\circ}C.$$

3. $V_{peak} = |(V_{out max} - V_{offset})|$. Periodicity of V_{peak} : $sin(2\alpha)$ and $cos(2\alpha)$ respectively.

$$4. \quad TC_{Vpeak} = 100 \times \frac{V_{peak(T_2)} - V_{peak(T_1)}}{V_{peak(T_1)} \times 190^{\circ}C} \ \, \text{where } T_1 = -40 \, ^{\circ}C; \, T_2 = 150 \, ^{\circ}C.$$

5. Bridge resistance between pins 8 and 4, pins 7 and 3, pins 5 and 1, and pins 6 and 2.

$$6. \quad TC_{Rbridge} = 100 \times \frac{R_{bridge(T_2)} - R_{bridge(T_1)}}{R_{bridge(T_1)} \times 190^{\circ}C} \quad \text{where } T_1 = -40 \, ^{\circ}C; \, T_2 = 150 \, ^{\circ}C.$$

7.
$$TC_{Voffset} = \frac{V_{offset(T_2)} - V_{offset(T_1)}}{190^{\circ}C}$$
 where $T_1 = -40^{\circ}C$; $T_2 = 150^{\circ}C$.

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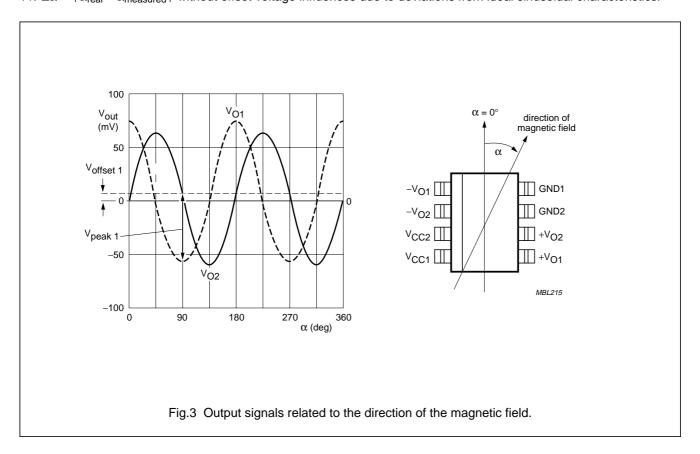
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$$\begin{split} 8. \quad FH_1 &= 100 \times \left| \frac{V_{O1(67.5^\circ) \ 135^\circ \Rightarrow 45^\circ - V_{O1(67.5^\circ) \ 45^\circ \Rightarrow 135^\circ}}{2 \times V_{peak1}} \right| \,. \\ FH_2 &= 100 \times \left| \frac{V_{O2(22.5^\circ) \ 90^\circ \Rightarrow 0^\circ - V_{O2(22.5^\circ) \ 0^\circ \Rightarrow 90^\circ}}{2 \times V_{peak2}} \right| \,. \end{split}$$

$$9. \quad k = 100 \times \frac{V_{peak1}}{V_{peak2}}.$$

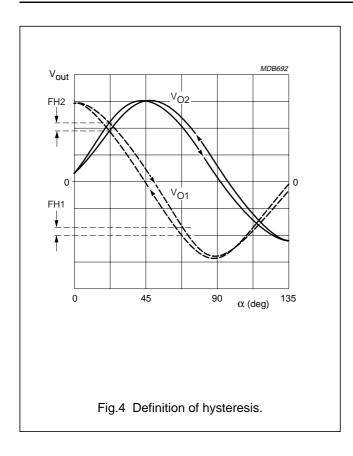
10.
$$TC_k = 100 \times \frac{k_{T_2} - k_{T_1}}{k_{T_1} \times 190^{\circ}C}$$
 where $T_1 = -40 \,^{\circ}C$; $T_2 = 150 \,^{\circ}C$.

11. $\Delta \alpha = |\alpha_{real} - \alpha_{measured}|$ without offset voltage influences due to deviations from ideal sinusoidal characteristics.



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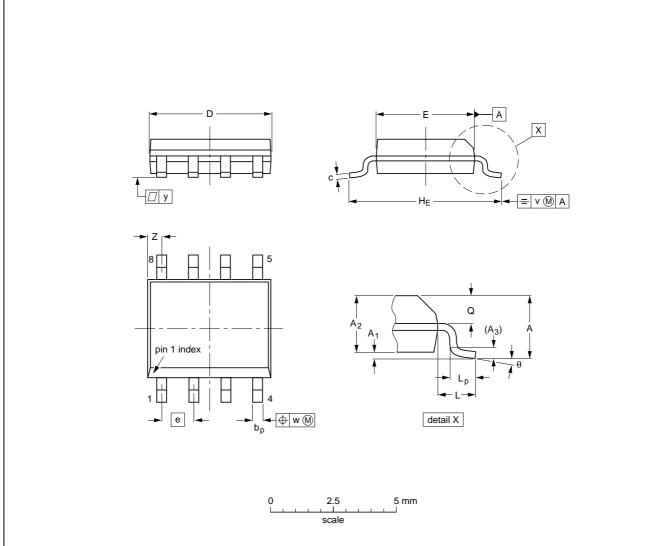
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PACKAGE OUTLINE

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ICCUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT96-1	076E03	MS-012				99-12-27 03-02-18	

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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